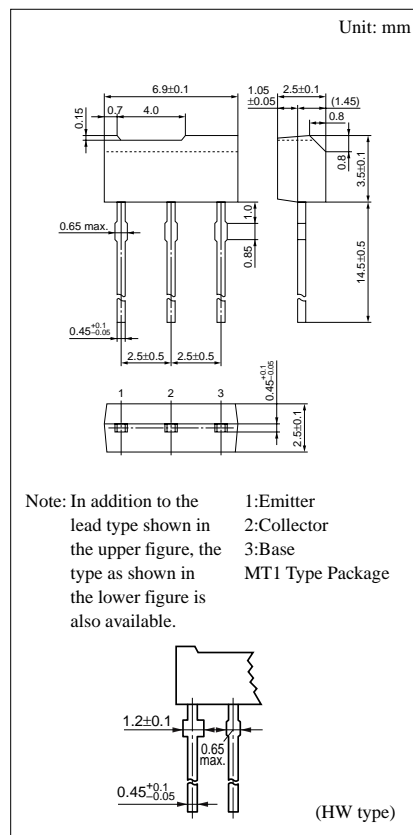


Silicon NPN epitaxial planer type

■ Features

- Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	60	V
Collector to emitter voltage	V_{CEO}	50	V
Emitter to base voltage	V_{EBO}	7	V
Peak collector current	I_{CP}	1	A
Collector current	I_C	500	mA
Collector power dissipation	P_C	600	mW
Junction temperature	T_j	150	$^{\circ}\text{C}$
Storage temperature	T_{stg}	$-55 \sim +150$	$^{\circ}\text{C}$



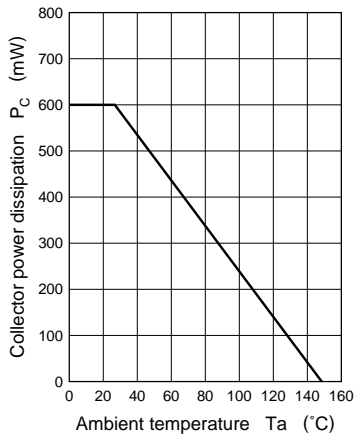
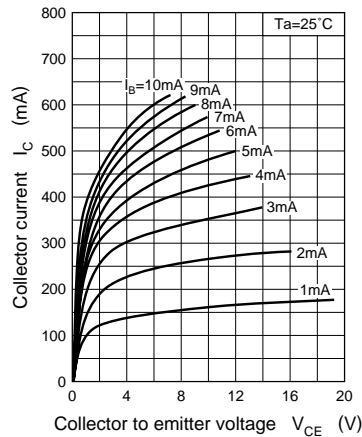
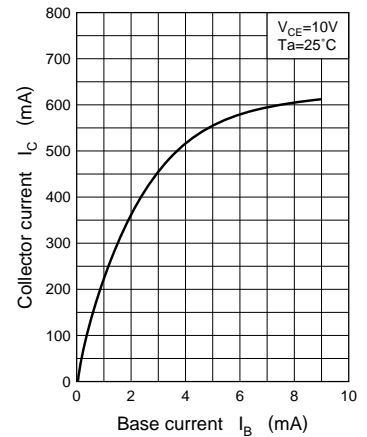
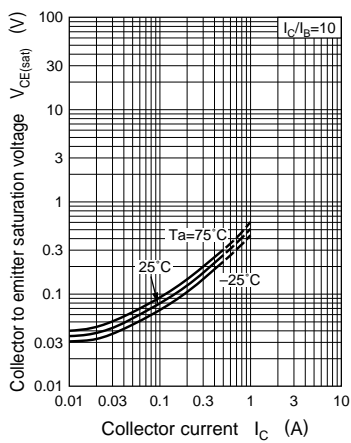
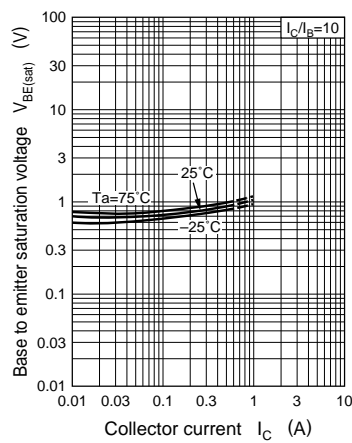
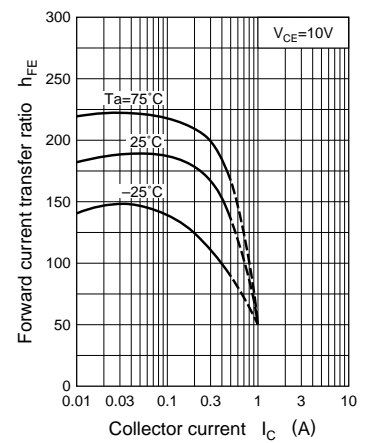
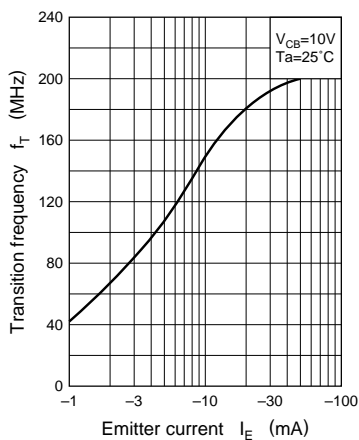
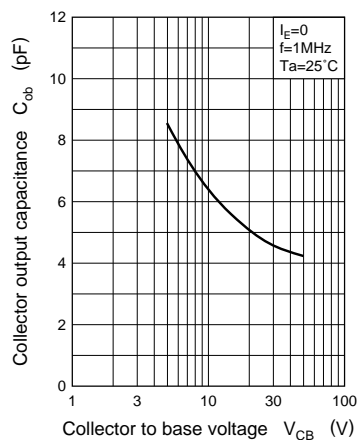
■ Electrical Characteristics (Ta=25°C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = 20V, I_E = 0$			0.1	μA
	I_{CEO}	$V_{CE} = 20V, I_B = 0$			1	μA
Collector to base voltage	V_{CBO}	$I_C = 10\mu A, I_E = 0$	60			V
Collector to emitter voltage	V_{CEO}	$I_C = 2mA, I_B = 0$	50			V
Emitter to base voltage	V_{EBO}	$I_E = 10\mu A, I_C = 0$	7			V
Forward current transfer ratio	h_{FE1}^{*1}	$V_{CE} = 10V, I_C = 10mA^{*2}$	85	160	340	
	h_{FE2}	$V_{CE} = 10V, I_C = 500mA^{*2}$	40	90		
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = 300mA, I_B = 30mA^{*2}$		0.35	0.6	V
Transition frequency	f_T	$V_{CB} = 10V, I_E = -10mA, f = 200MHz$		200		MHz
Collector output capacitance	C_{ob}	$V_{CB} = 10V, I_E = 0, f = 1MHz$		6	15	pF

*2 Pulse measurement

^{*}1h_{FFI} Rank classification

Rank	Q	R	S
h_{FeI}	85 ~ 170	120 ~ 240	170 ~ 340

$P_C - T_a$  $I_C - V_{CE}$  $I_C - I_B$  $V_{CE(sat)} - I_C$  $V_{BE(sat)} - I_C$  $h_{FE} - I_C$  $f_T - I_E$  $C_{ob} - V_{CB}$  $V_{CER} - R_{BE}$ 